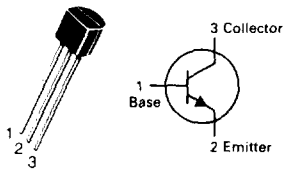
MPSH34

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



IF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +135	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

Refer to MPSH24 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 7.0 mAdc, V_{CE} = 15 Vdc) (I_C = 20 mAdc, V_{CE} = 2.0 Vdc)	h_{FE}	 40 15	 — —	 — —	—
Collector-Emitter Saturation Voltage (I_C = 7.0 mAdc, I_B = 2.0 mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage (I_C = 7.0 mAdc, V_{CE} = 15 Vdc)	$V_{BE(on)}$	—	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 15 mAdc, V_{CE} = 15 Vdc, f = 100 MHz)	f_T	500	720	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	0.25	0.32	pF